



STGP10NB60S

STGP10NB60SFP- STGB10NB60S

N-CHANNEL 10A - 600V - TO-220/TO-220FP/D²PAK
PowerMESH™ IGBT

Table 1: General Features

TYPE	V _{CES}	V _{CE(sat)} (Max) @25°C	I _C @100°C
STGP10NB60S	600 V	< 1.7 V	10 A
STGP10NB60SFP	600 V	< 1.7 V	10 A
STGB10NB60S	600 V	< 1.7 V	10 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- VERY LOW ON-VOLTAGE DROP (V_{cesat})
- HIGH CURRENT CAPABILITY
- OFF LOSSES INCLUDE TAIL CURRENT

DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "S" identifies a family optimized achieve minimum on-voltage drop for low frequency applications (<1kHz).

APPLICATIONS

- LIGHT DIMMER
- STATIC RELAYS
- MOTOR CONTROL

Figure 1: Package

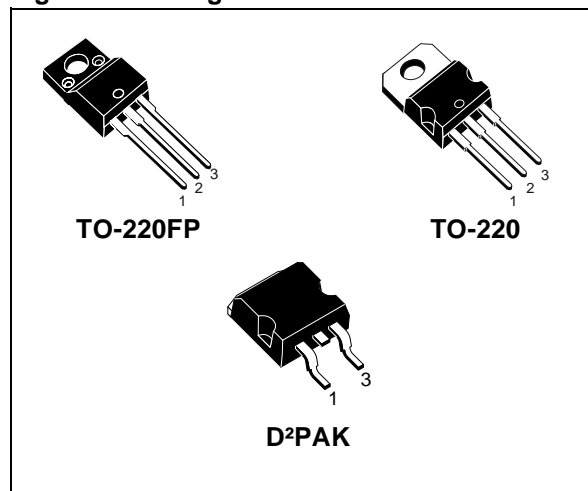


Figure 2: Internal Schematic Diagram

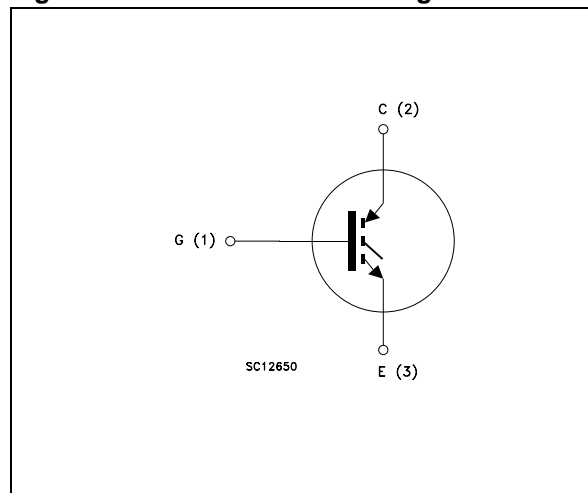


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGP10NB60S	GP10NB60S	TO-220	TUBE
STGP10NB60SFP	GP10NB60SFP	TO-220FP	TUBE
STGB10NB60ST4	GB10NB60S	D ² PAK	TAPE & REEL

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value		Unit
		TO-220/D ² PAK	TO-220FP	
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600		V
V _{ECR}	Reverse Battery Protection	20		V
V _{GE}	Gate-Emitter Voltage	± 20		V
I _C	Collector Current (continuous) at 25°C	20		A
I _C	Collector Current (continuous) at 100°C	10		A
I _{CM} (1)	Collector Current (pulsed)	80		A
P _{TOT}	Total Dissipation at T _C = 25°C	80	25	W
	Derating Factor	0.64	0.20	W/°C
V _{ISO}	Insulation Withstand Voltage A.C.(t=1sec, T _C =25°C)	--	2500	V
T _{stg}	Storage Temperature	- 55 to 150		°C
T _j	Operating Junction Temperature			

(1)Pulse width limited by max. junction temperature.

Table 4: Thermal Data

			Min.	Typ.	Max.	Unit
R _{thj-case}	Thermal Resistance Junction-case	TO-220 D ² PAK			1.56	°C/W
		TO-220FP			5.0	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient				62.5	°C/W
T _L	Maximum Lead Temperature for Soldering Purpose (1.6 mm from case, for 10 sec.)			300		°C

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)
Table 5: Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collectro-Emitter Breakdown Voltage	I _C = 250 μA, V _{GE} = 0	600			V
V _{BR(ECS)}	Emitter-Collector Breakdown Voltage	I _C = 1mA, V _{GE} = 0	20			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{GE} = Max Rating, T _C =25°C V _{CE} = Max Rating, T _C =125°C			10 100	μA μA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ± 20 V , V _{CE} = 0			±100	nA

Table 6: On

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} , I _C = 250 μA	2.5		5	V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	V _{GE} =15 V, I _C = 5 A,		1.15		V
		V _{GE} =15 V, I _C = 10 A,		1.35	1.7	V
		V _{GE} =15 V, I _C = 10 A, T _j = 125°C		1.25		V

ELECTRICAL CHARACTERISTICS (CONTINUED)

Table 7: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{CE} = 25 \text{ V}$, $I_C = 10 \text{ A}$		7		S
C_{ies}	Input Capacitance	$V_{CE} = 25 \text{ V}$, $f = 1 \text{ MHz}$, $V_{GE} = 0$		610		pF
C_{oes}	Output Capacitance			65		pF
C_{res}	Reverse Transfer Capacitance			12		pF
Q_g	Total Gate Charge	$V_{CE} = 400 \text{ V}$, $I_C = 10 \text{ A}$, $V_{GE} = 15 \text{ V}$ (see Figure 20)		33		nC
I_{CL}	Latching Current	$V_{clamp} = 480 \text{ V}$, $T_j = 150^\circ\text{C}$ $R_G = 1 \text{ k}\Omega$	20			A

Table 8: Switching On

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Current Rise Time	$V_{CC} = 480 \text{ V}$, $I_C = 10 \text{ A}$ $R_G=1\text{K}\Omega$ $V_{GE} = 15 \text{ V}$ (see Figure 18)		0.7 0.46		μs μs
$(di/dt)_{on}$ E_{on} (1)	Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 480 \text{ V}$, $I_C = 10 \text{ A}$ $R_G=1\text{K}\Omega$ $V_{GE} = 15 \text{ V}$, $T_j = 125^\circ\text{C}$		8 0.6		$\text{A}/\mu\text{s}$ mJ

Table 9: Switching Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c	Cross-Over Time	$V_{CC} = 480 \text{ V}$, $I_C = 10 \text{ A}$, $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$ $T_J = 25^\circ\text{C}$ (see Figure 18)		2.2		μs
$t_r(V_{off})$	Off Voltage Rise Time			1.2		μs
t_f	Current Fall Time			1.2		μs
$E_{off} (**)$	Turn-off Switching Loss			5.0		mJ
t_c	Cross-Over Time	$V_{CC} = 480 \text{ V}$, $I_C = 10 \text{ A}$, $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$ $T_J = 125^\circ\text{C}$ (see Figure 18)		3.8		μs
$t_r(V_{off})$	Off Voltage Rise Time			1.2		μs
t_f	Current Fall Time			1.9		μs
$E_{off} (**)$	Turn-off Switching Loss			8.0		mJ

(1)Pulse width limited by max. junction temperature.

(**)Losses Include Also the Tail (Jedec Standardization)

Figure 3: Output Characteristics

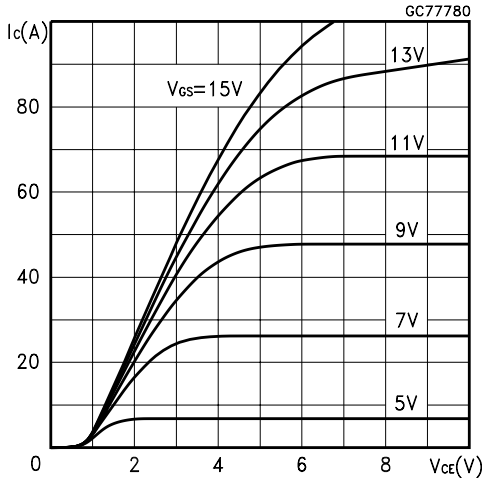


Figure 4: Transconductance

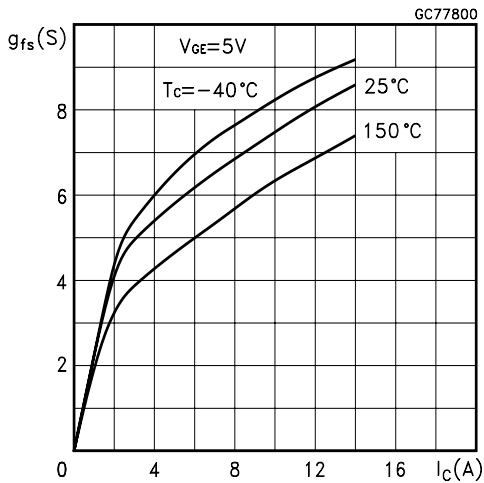


Figure 5: Collector-Emitter On Voltage vs Collector Current

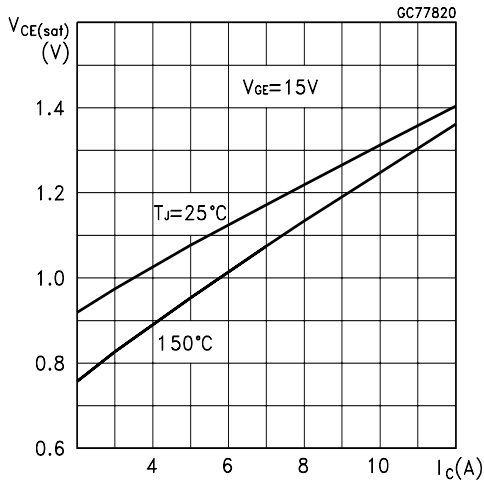


Figure 6: Transfer Characteristics

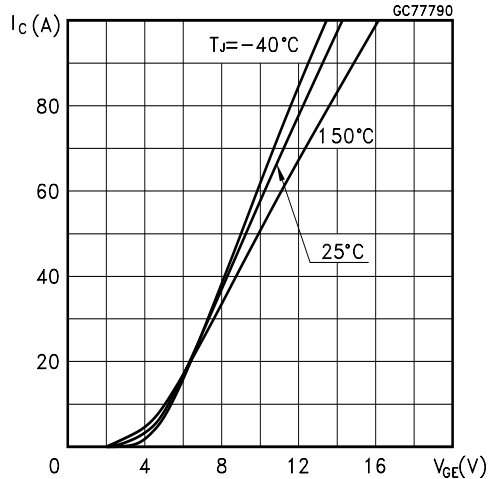


Figure 7: Collector-Emitter On Voltage vs Temperature

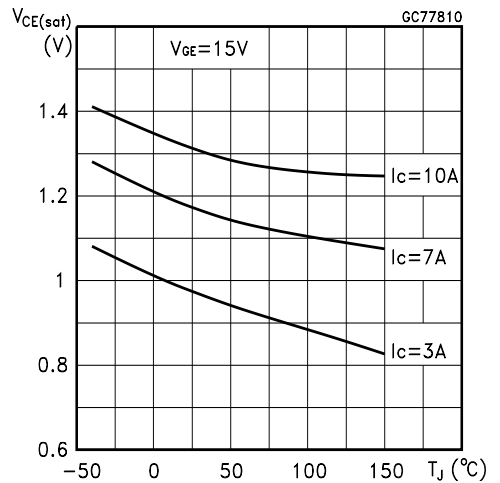


Figure 8: Gate Threshold vs Temperature

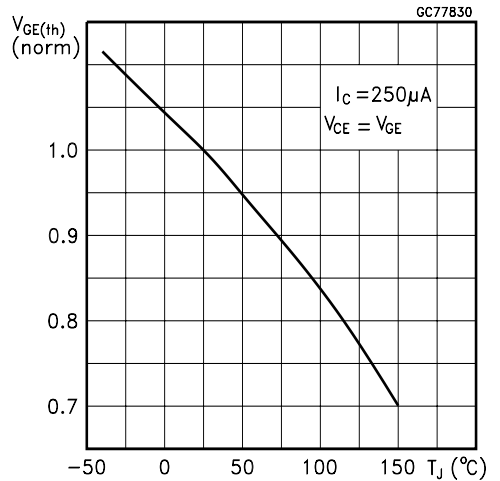


Figure 9: Capacitance Variations

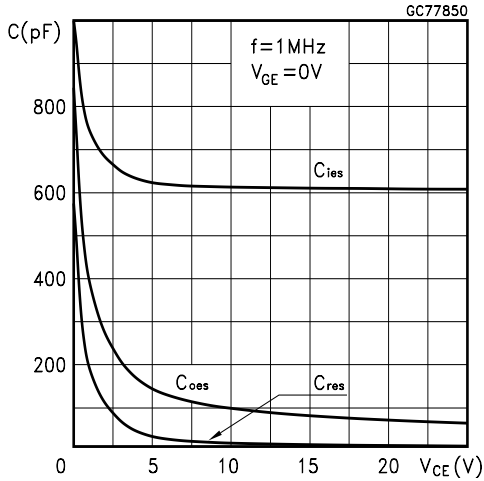


Figure 10: Off Losses vs Gate Resistance

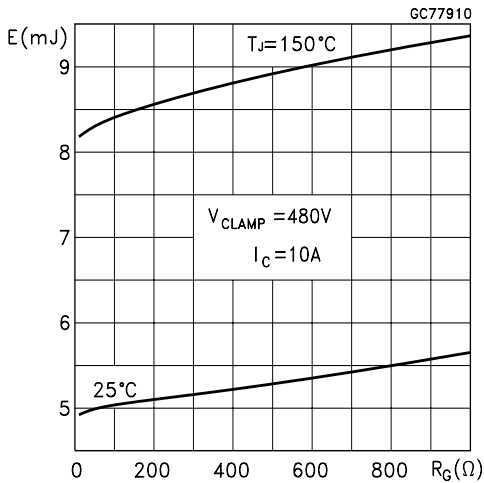


Figure 11: Normalized Breakdown Voltage vs Temperature

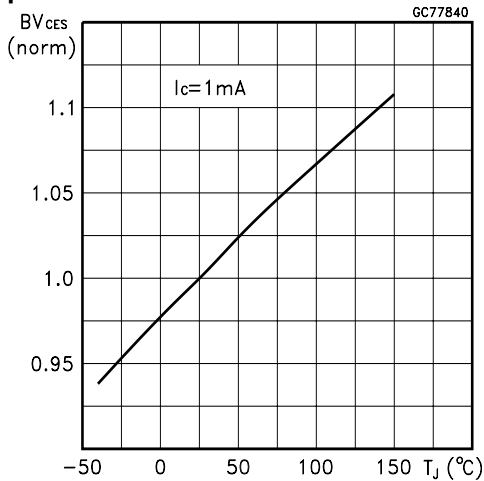


Figure 12: Gate Charge vs Gate-Emitter Voltage

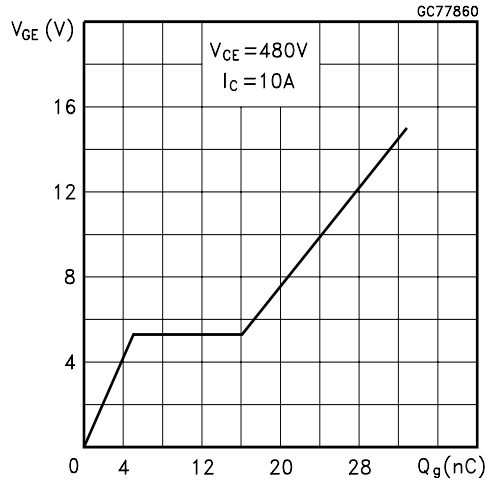


Figure 13: Off Losses vs Temperature

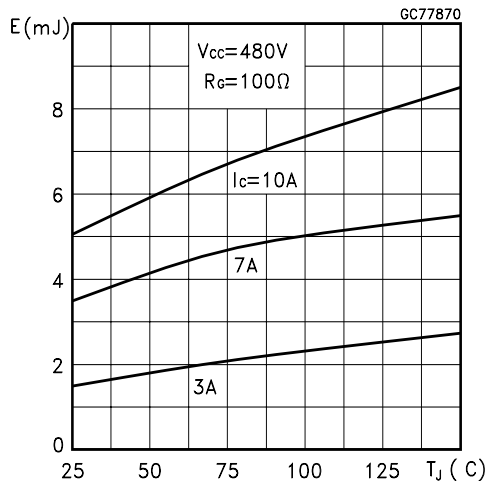


Figure 14: Off Losses vs Collector Current

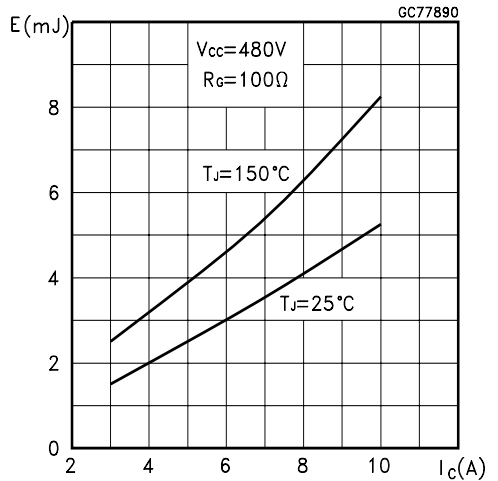
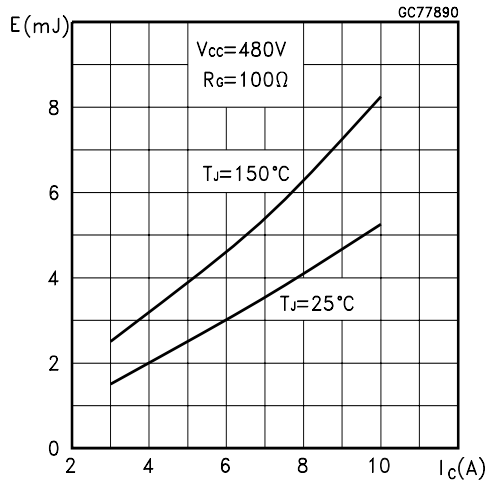
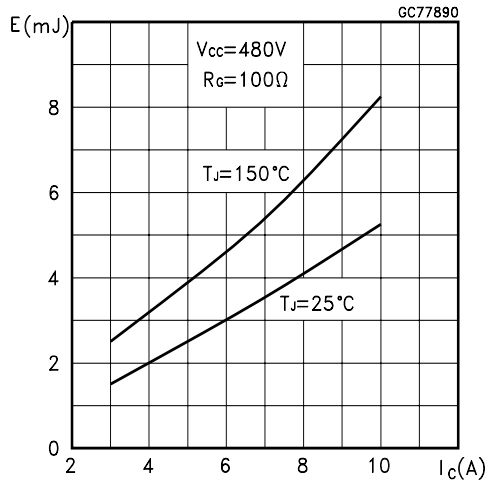


Figure 15: Thermal Impedance For TO-220/ D²PAK

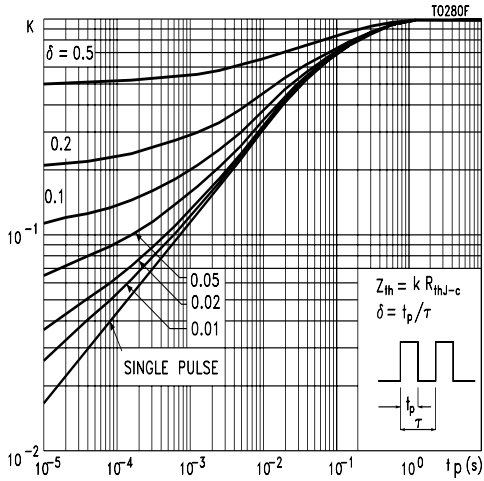


Figure 16: Turn-Off SOA

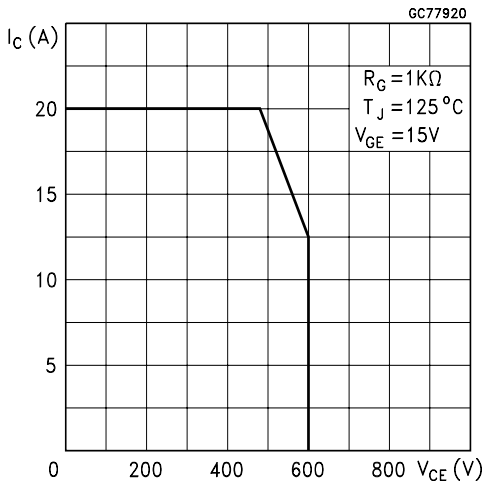


Figure 17: Thermal Impedance For TO-220FP

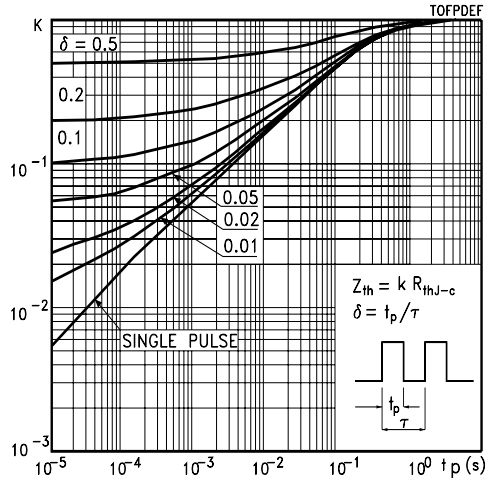


Figure 18: Test Circuit for Inductive Load Switching

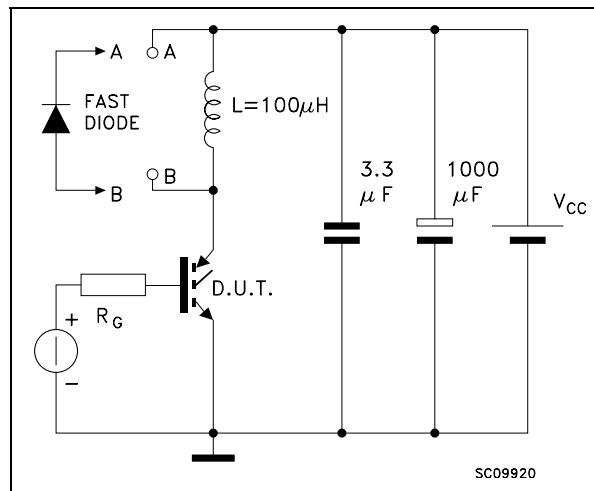


Figure 19: Switching Waveforms

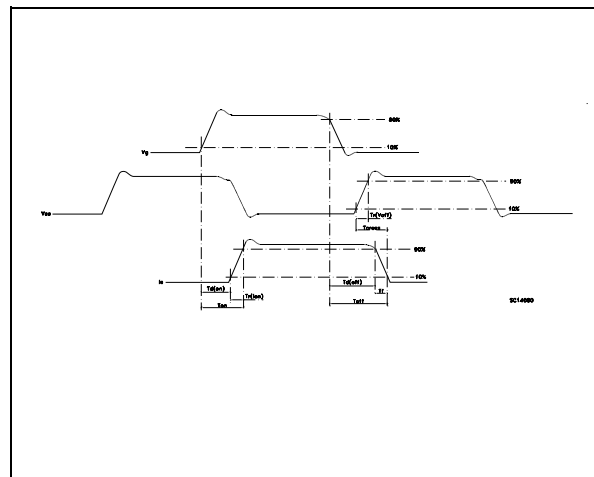
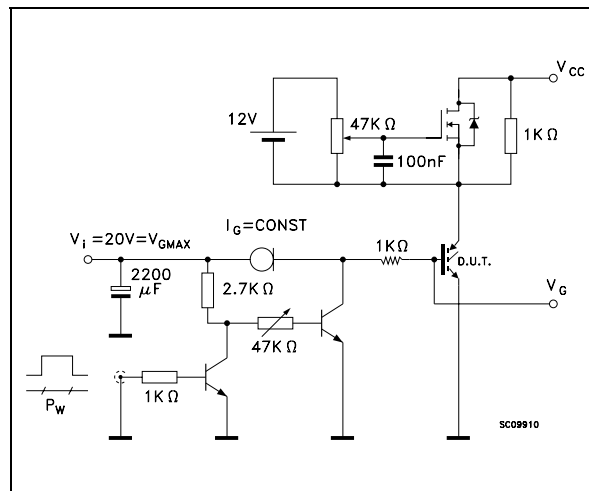
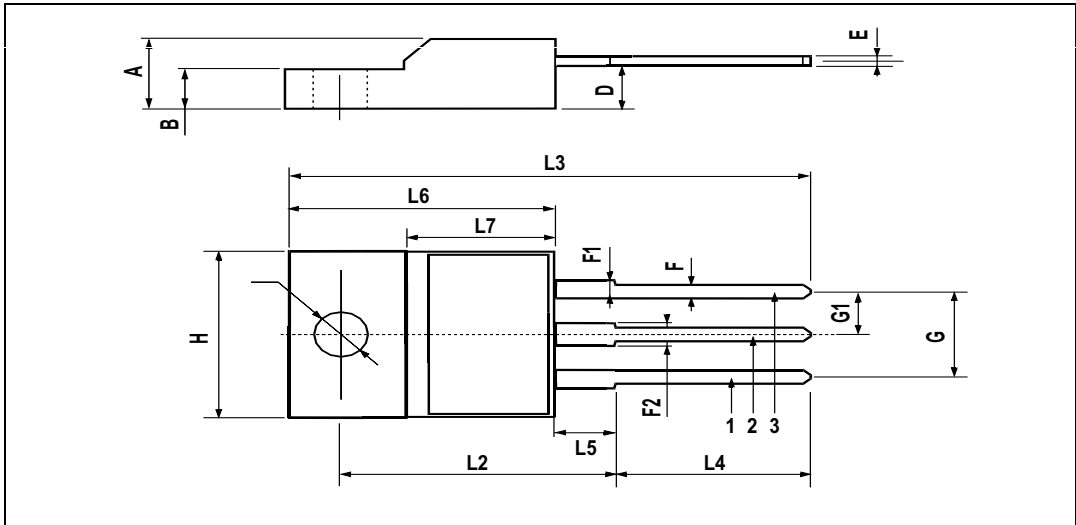


Figure 20: Gate Charge Test Circuit



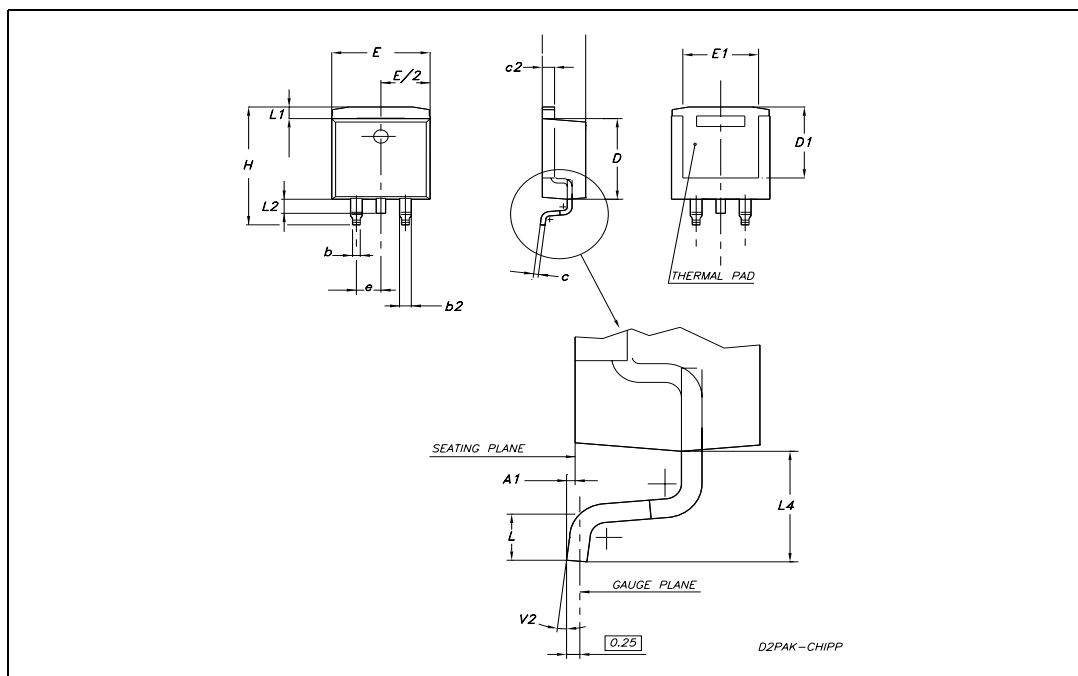
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
∅	3		3.2	0.118		0.126

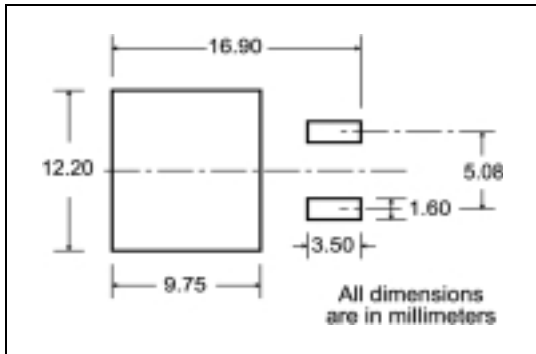


TO-263 (D²PAK) MECHANICAL DATA

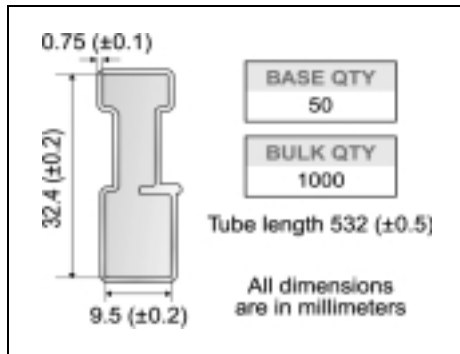
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.32		4.57	0.178		0.180
A1	0.00		0.25	0.00		0.009
b	0.71		0.91	0.028		0.350
b2	1.15		1.40	0.045		0.055
c	0.46		0.61	0.018		0.024
c2	1.22		1.40	0.048		0.055
D	8.89	9.02	9.40	0.350	0.355	0.370
D1	8.01			0.315		
E	10.04		10.28	0.395		0.404
e		2.54			0.010	
H	13.10		13.70	0.515		0.540
L	1.30		1.70	0.051		0.067
L1	1.15		1.39	0.045		0.054
L2	1.27		1.77	0.050		0.069
L4	2.70		3.10	0.106		0.122
V2	0°		8°	0°		8°



D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

* on sales type

Table 10: Revision History

Date	Revision	Description of Changes
10-Nov-2004	1	First release
28-Feb-2005	2	Some values changed in table 6

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